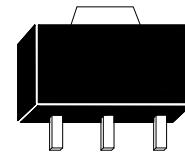


N-CHANNEL MOSFET

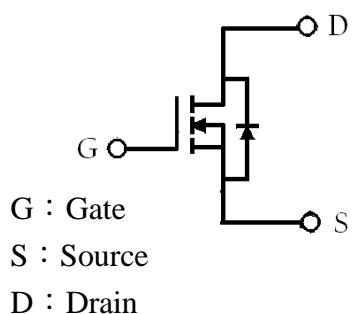
Features:

- Low on-resistance
- High speed switching
- Low-voltage drive
- Easily designed drive circuits
- Pb-free lead plating and halogen-free package



G D S

SOT-89



BVDSS	30V
Id	6.8A
RDS(on)@VGS=10V, Id=5.8A	25mΩ (typ)
RDS(on)@VGS=4.5V, Id=5A	27mΩ (typ)

Absolute Maximum Ratings ($T_a=25^\circ C$)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V_{DSS}	30	V
Gate-Source Voltage	V_{GSS}	± 12	V
Continuous Drain Current @ $V_{GS}=10V$, $T_a=25^\circ C$	I_D	6.8	A
Continuous Drain Current @ $V_{GS}=10V$, $T_a=100^\circ C$	I_D	4.3	A
Pulsed Drain Current	I_{DM}	30 *1	A
Total Power Dissipation	P_D	2 *2	W
Operating Junction and Storage Temperature Range	T_j ; T_{stg}	-55~+150	°C

Note : *1. Pulse Width $\leq 300\mu s$, Duty cycle $\leq 2\%$

*2. When the device is surface mounted on 1 in² copper pad of FR-4 board with 2 oz. copper, $t \leq 10s$.

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance, Junction-to-Ambient	$R_{th,ja}$	62.5	°C/W

Note : Surface mounted on 1 in² copper pad of FR-4 board with 2 oz. copper, $t \leq 10s$.



Electrical Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BVDSS*	30	-	-	V	V _{GS} =0, I _D =10μA
V _{GS(th)}	0.5	0.8	1.2	V	V _{DS} =V _{GS} , I _D =250μA
I _{GSS}	-	-	±100	nA	V _{GS} =±12V, V _{DS} =0
I _{DSS}	-	-	1	μA	V _{DS} =24V, V _{GS} =0
R _{DSON} *	-	25	28	m	V _{GS} =10V, I _D =5.8A
	-	27	33		V _{GS} =4.5V, I _D =5A
	-		45		V _{GS} =2.5V, I _D =4A
	-		85		V _{GS} =1.8V, I _D =1A
G _{FS}	-	11	-	S	V _{DS} =5V, I _D =5A
Dynamic					
C _{iss}	-	1052	-	pF	V _{DS} =15V, V _{GS} =0, f=1MHz
C _{oss}	-	57	-		
C _{rss}	-	54	-		
t _{d(ON)}	-	5	-	ns	V _{DS} =15V, I _D =5.8A, V _{GS} =10V, R _{GEN} =3Ω
t _r	-	2.4	-		
t _{d(OFF)}	-	16	-		
t _f	-	5	-		
Q _g	-	9.7	-	nC	V _{DS} =15V, I _D =5.8A, V _{GS} =4.5V
Q _{gs}	-	2.7	-		
Q _{gd}	-	4.1	-		
Source-Drain Diode					
*I _S	-	-	1.2	A	
*V _{SD}	-	-	1.2	V	V _{GS} =0V, I _S =1.2A
*t _{rr}	-	18	-	ns	I _F =6.8A, dI _F /dt=100A/μs
*Q _{rr}	-	10	-	nC	

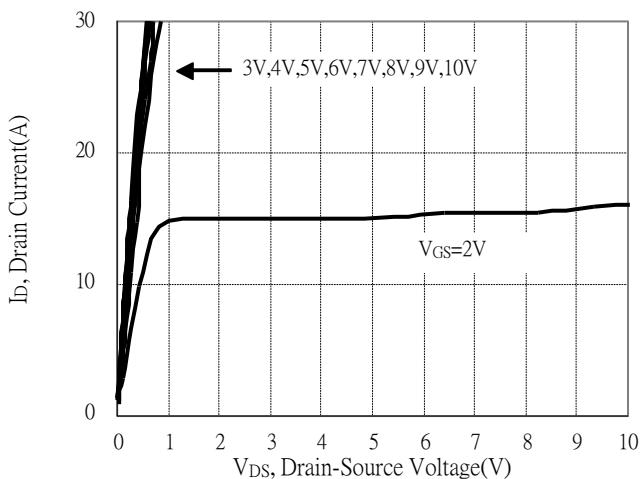
*Pulse Test : Pulse Width ≤380μs, Duty Cycle≤2%

Ordering Information

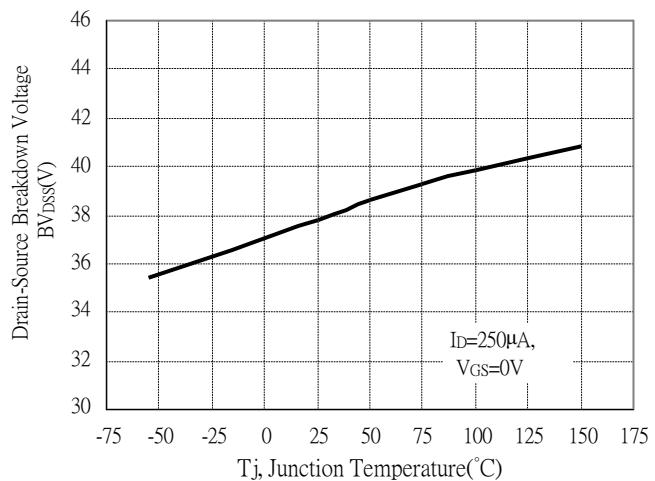
Device	Package	Shipping
KWN2306AM3	SOT-89 (Pb-free lead plating & halogen-free package)	1000 pcs / Tape & Reel

Typical Characteristics

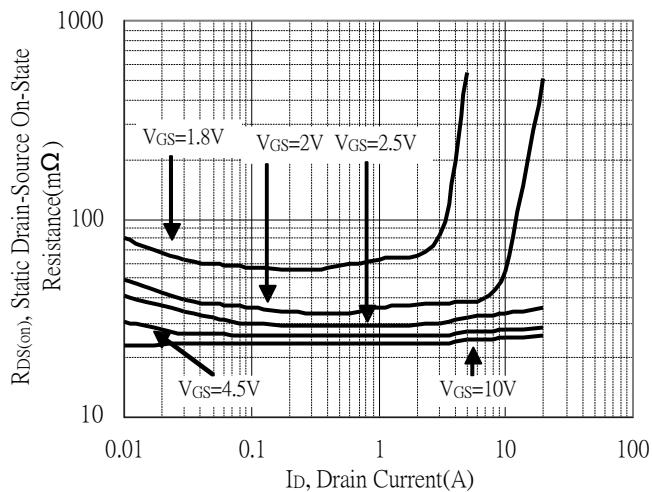
Typical Output Characteristics



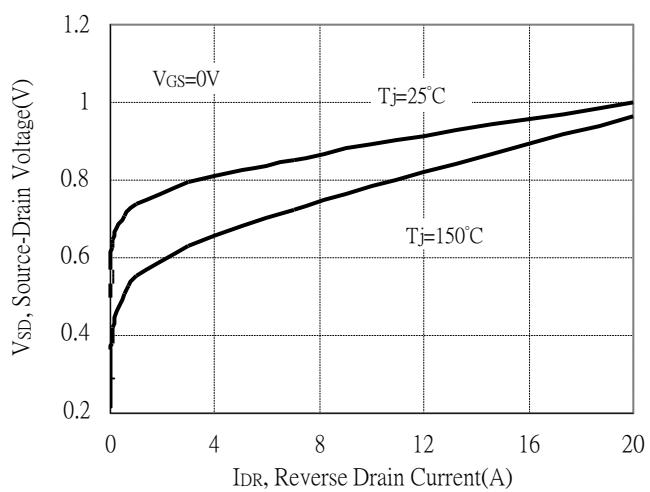
Breakdown Voltage vs Ambient Temperature



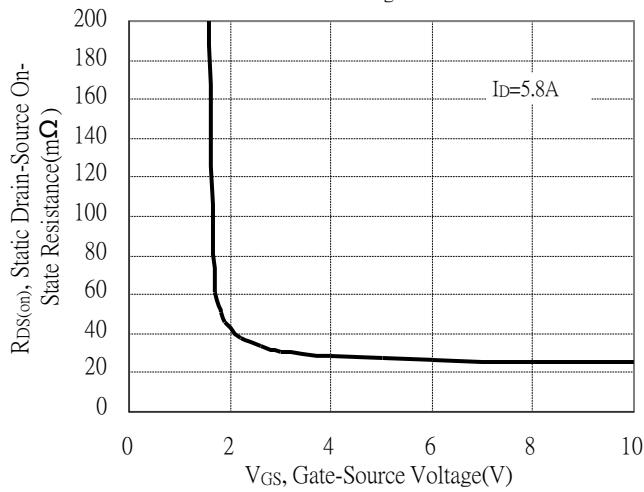
Static Drain-Source On-State resistance vs Drain Current



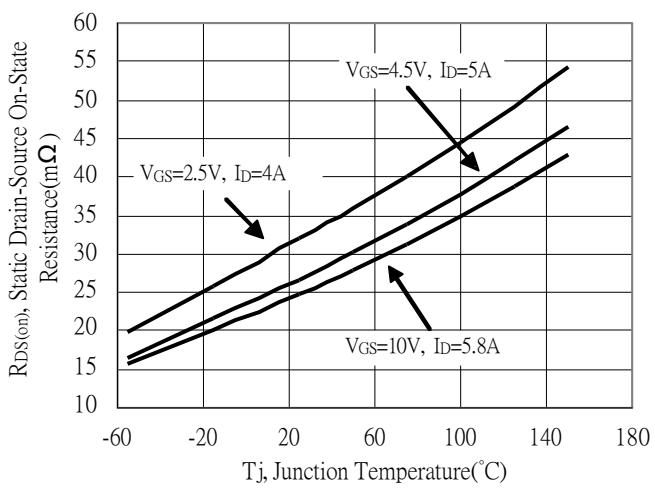
Reverse Drain Current vs Source-Drain Voltage



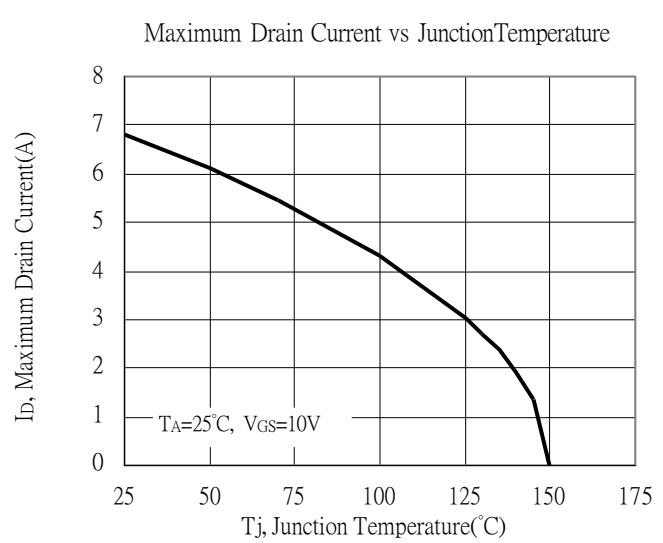
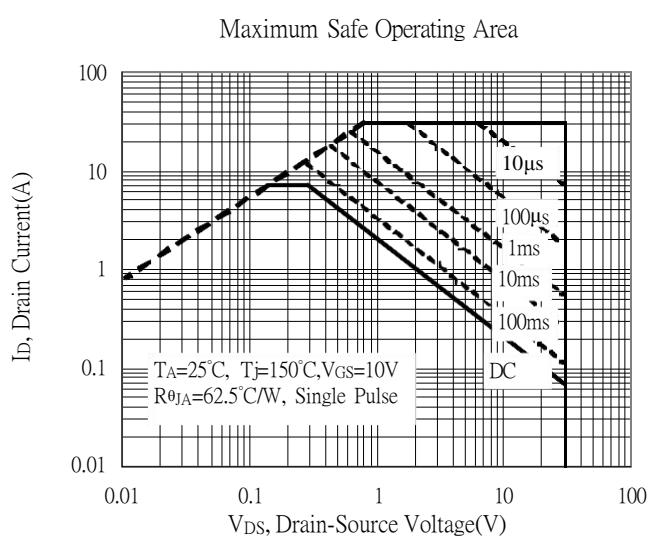
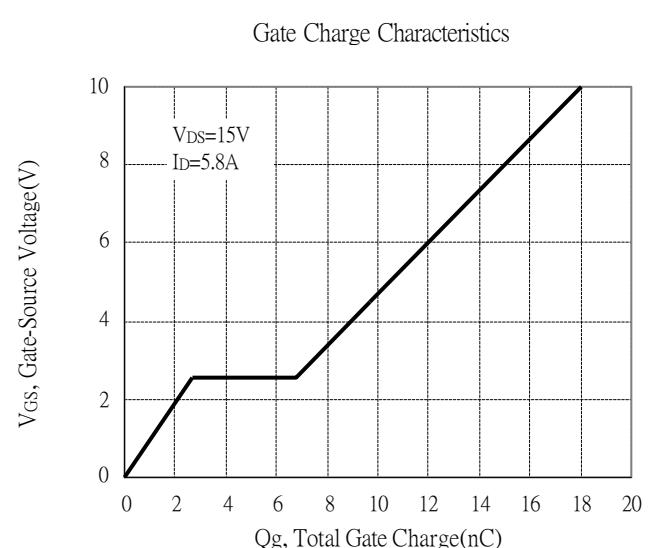
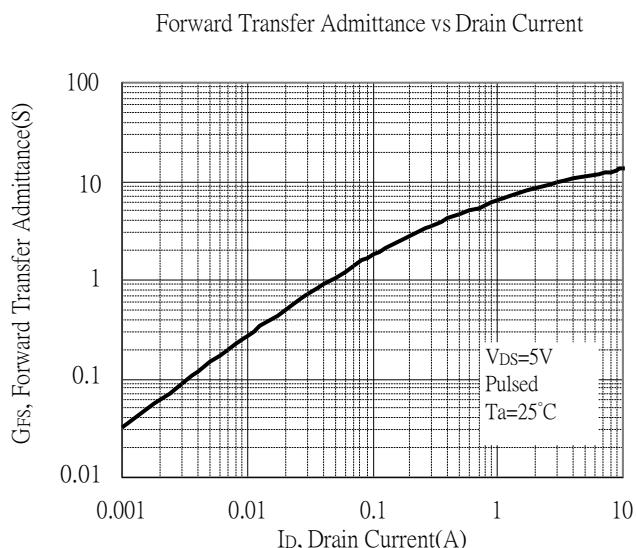
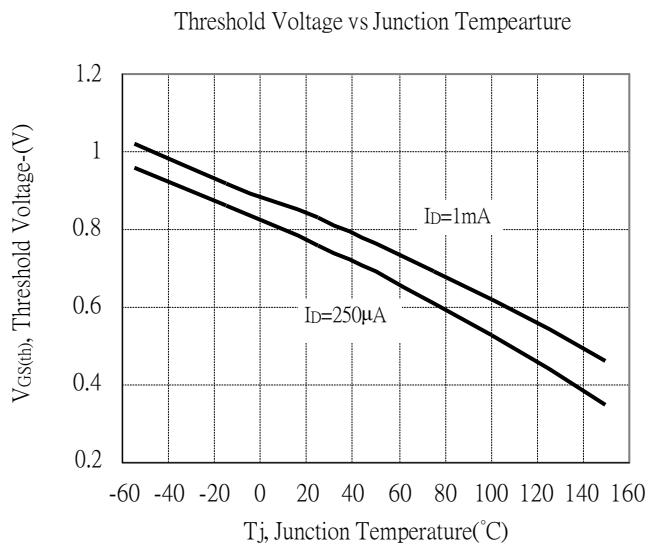
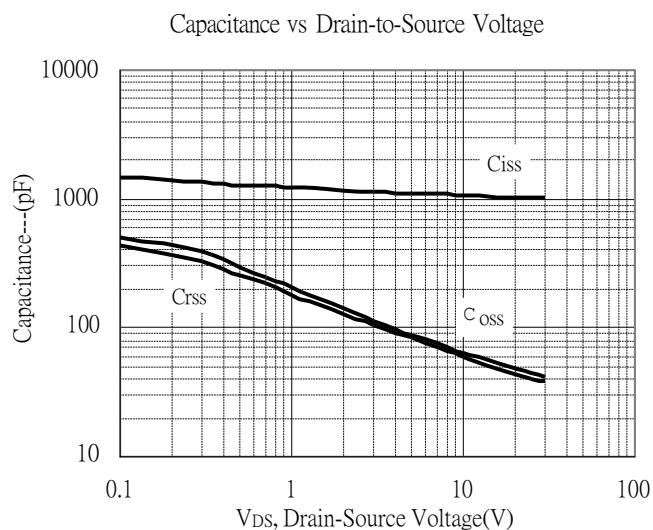
Static Drain-Source On-State Resistance vs Gate-Source Voltage



Drain-Source On-State Resistance vs Junction Temperature

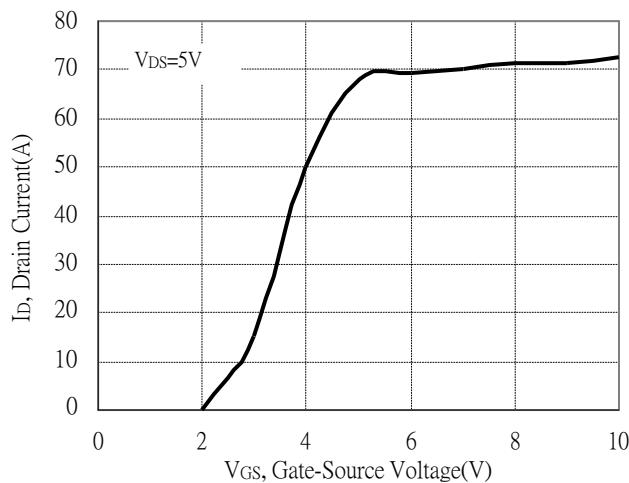


Typical Characteristics(Cont.)

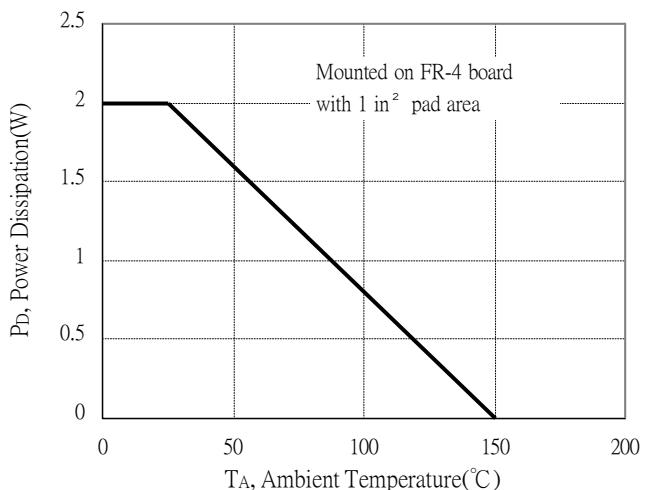


Typical Characteristics(Cont.)

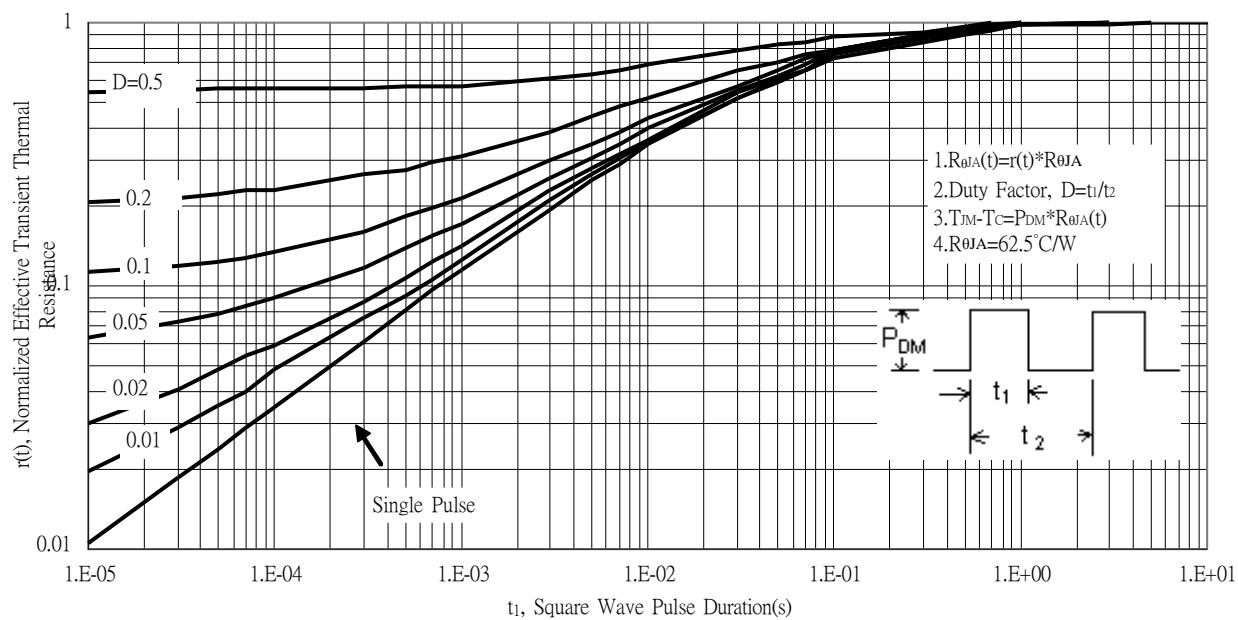
Typical Transfer Characteristics



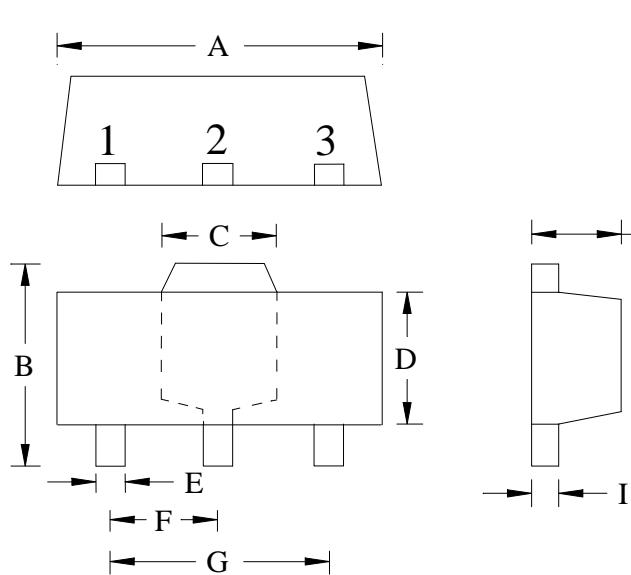
Power Derating Curve



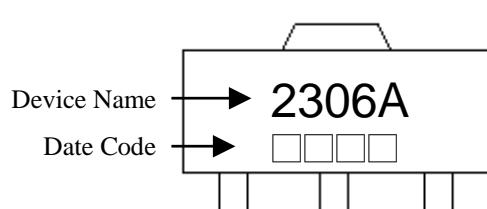
Transient Thermal Response Curves



SOT-89 Dimension



Marking:



Style: Pin 1. Gate 2. Drain 3. Source

3-Lead SOT-89 Plastic
Surface Mounted Package
Code: M3

*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1732	0.1811	4.40	4.60	F	0.0583	0.0598	1.48	1.527
B	0.1594	0.1673	4.05	4.25	G	0.1165	0.1197	2.96	3.04
C	0.0591	0.0663	1.50	1.70	H	0.0551	0.0630	1.40	1.60
D	0.0945	0.1024	2.40	2.60	I	0.0138	0.0161	0.35	0.41
E	0.01417	0.0201	0.36	0.51					